

GROWTH AND CHARACTERISATION OF MANGANESE DOPED GALLIUM NITRIDE NANO STRUCTURES

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Gallium nitride is one of the most promising material among the Group III nitrides. Manganese doped GaN nanowires were mainly used in spintronic applications. We report the Growth mechanism of Mn doped GaN nanowires like structures and Scanning electron Microscopy (SEM), Raman Studies, Electron Paramagnetic Resonance (EPR) results. From SEM results indicates Mn doped GaN nano wires formation. Raman studies indicates GaMnN formation and EPR results indicates Mn incorporation in GaN. Results will be discussed in detail.